

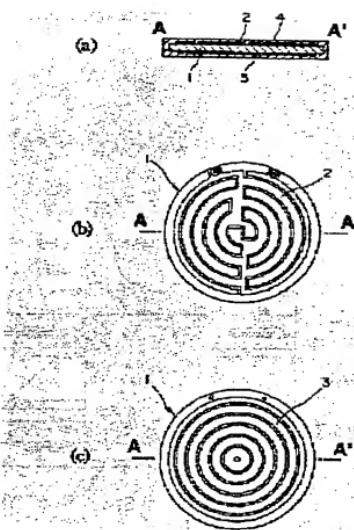
ELECTROSTATIC CHUCK

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 Inventor: KANO MASAKI; KUROSAWA YUKIO; ARAI NOBUO
 Applicant: SHIN ETSU CHEM CO LTD
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Abstract of JP10080168

PROBLEM TO BE SOLVED: To provide an electrostatic chuck which can restrain a warpage from being generated in its manufacture even when a support substrate is thin and compact by a method in which an electrostatic chuck pattern is formed on the surface of the substrate and a pattern whose shape is identical to, or similar to, that of the pattern on the surface or a heat-generating pattern is formed on its rear.

SOLUTION: In an electrostatic chuck, an electrode pattern 2, for the electrostatic chuck, which is conductive is formed on the surface of a support substrate 1 which is composed of an electric insulating ceramic, and a pattern 3 is formed on its rear. In this case, protective layers 4 are formed so as to respectively cover the patterns 2, 3 on the surface and the rear. In this manner, the pattern 2 for the electrostatic chuck is formed on the surface of the support substrate, and the pattern 3 whose shape is identical to, or similar to, that of the pattern on the surface is formed on the rear. Thereby, it is possible to prevent a warpage from being generated in its manufacture, its heating performance or its cooling performance which heats or cools a wafer is enhanced, and its stability can be enhanced in its heating operation or its cooling operation.



Japanese Patent Application Laid-Open No. 10-80168

[Title of the Invention]

ELECTROSTATIC CHUCK

[Abstract]

5 [Purpose] To provide an electrostatic chuck comprising electrode patterns for the electrostatic chuck bonded to the surface of a supporting substrate made of an insulating ceramic and patterns same as or similar to the electrode patterns for the above-mentioned electrostatic chuck bonded to the rear face.

10 [Effect] According to the present invention, with respect to an electrostatic chuck, more particularly an electrostatic chuck provided with a heater and thus having a heating function, for electrostatically attracting a wafer or the like to be a supporting substrate of a semiconductor device, electrostatic chuck patterns are formed on the surface of the supporting substrate and

15 patterns or heating patterns same as or similar to the electrostatic chuck patterns are formed on the rear face, so that warp can be suppressed in the manufacturing process even if the substrate is thin and compact. Also, thermal deformation and warp of the electrostatic chuck or the electrostatic chuck provided with a heater can be prevented when a wafer is heated or

20 cooled and thus the electrostatic attraction power can be stabilized. Consequently, an electrostatic chuck and an electrostatic chuck provided with a heater with excellent properties and capabilities can be provided at a low cost.

1. An electrostatic chuck comprising electrode patterns for the electrostatic chuck bonded to the surface of a supporting substrate made of an insulating ceramic and patterns same as or similar to the electrode patterns for the electrostatic chuck bonded to the rear face.
5. The electrostatic chuck according to claim 1, wherein at least a portion of the patterns in the rear face are connected to an electric power source so as to be a heating pattern composing as a heating part.
3. The electrostatic chuck according to claim 1 or claim 2, wherein the electrode patterns for the electrostatic chuck in the surface and the patterns 10 in the rear face are made of materials having thermal expansion coefficients substantially same as each other.
4. The electrostatic chuck according to any of claims 1 to 3, wherein the electrode patterns for the electrostatic chuck in the surface and the patterns in the rear face have the substantially same thickness.
15. 5. The electrostatic chuck according to any of claims 1 to 4, wherein the supporting substrate is made of AlN, BN, a compounded body of AlN and BN, PBN or SiO₂.
6. The electrostatic chuck according to any of claims 1 to 5, wherein the supporting substrate is formed by a chemical vapor deposition method or a 20 powder sintering method and the patterns in the surface and the rear face are respectively formed by a chemical vapor deposition method.
7. The electrostatic chuck according to any of claims 1 to 6, wherein protection layers having substantially same thermal expansion coefficient as that of the supporting substrate are formed so as to cover the respective 25 patterns in the surface and the rear face.

8. The electrostatic chuck according to claim 7, wherein the protection layers are made of AlN, BN, a compounded body of AlN and BN, PBN or SiO₂.
9. The electrostatic chuck according to claim 7 or claim 8, wherein the protection layers are made by a chemical vapor deposition method.

[Detailed Description of the Invention]

[0001]

10 [Industrial Field of the Invention]

The invention relates to an electrostatic chuck electrostatically attracting a wafer or the like to be a substrate of a semiconductor device and to an electrostatic chuck provided with a heater and thus having a heating function.

15 [0002]

[Prior Art and Problems to be Solved by the Invention]

An electrostatic chuck has been employed for electrostatically attracting and supporting a wafer in a molecular beam epitaxy, CVD, sputtering, or etching step or the like in the recent semiconductor device fabrication process and along with the tendency of higher temperature treatment in the fabrication process, a material of an electrostatic chuck has been shifted from resins to ceramics (reference to Japanese published unexamined Application Nos. 52-67353 and 59-124140) and recently, ceramic heaters provided with electrostatic chucks comprising ceramic heaters and electrostatic chucks united to each other have been proposed

(Japanese published unexamined Application Nos. 5 - 109876 and 5-129210).

[0003]

In this case, at the time of forming a film by molecular beam epitaxy,

5 CVD, sputtering or the like, since the temperature of a wafer greatly affects the properties of the film and the film formation speed, it has been required to improve the heating evenness of the wafer. Further, in the case of drying etching, since the temperature of a wafer greatly affects the etching shape, selective ratio, distribution and the like of fine etching, it has been
10 required to improve the cooling property for cooling the wafer.

[0004]

In manufacturing the electrostatic chuck, electrode patterns for the electrostatic chuck are connected to a substrate and an insulating layer is formed thereon, and since the materials of the substrate, the insulating

15 layer, and the patterns differ one another and especially their thermal expansion coefficients differ one another, warp takes place owing to the thermal history during the fabrication process and if the warp is significant, at the time of finishing grinding of the surface of an insulating layer, a part of the pattern layer is exposed to the surface in some cases or even if it is
20 not exposed, the dielectric strength of the insulating layer may be decreased to result in a defective product. Further, even if the finishing grinding is carried out well, thermal deformation or warp of the electrostatic chuck occurs at the time of heating or cooling a wafer attributed to the difference of the thermal expansion coefficients and the subsequent unstable attracting
25 force of the electrostatic chuck at the time of heating and cooling has been a

problem. One means for solving the problem is to use a thick substrate, however it results in increase of the heat capacity and increase of the electric power consumption and moreover, it takes longer to heat or cool the substrate and it results in cost up and accordingly, it is desirable to use a

5 thin and compact substrate, if possible. However, if a thin substrate is used, the above-mentioned problems is generated and therefore, it is obliged to use a thick substrate.

[0005]

The invention is accomplished to solve the above-mentioned

10 problems and aims to provide an electrostatic chuck or an electrostatic chuck provided with a heater whose warp in the manufacturing process is slight even if a thin and compact substrate is used and that is capable of providing electrostatic attracting force stable from a low temperature to a high temperature.

15 [0006]

[Means for Solving the Problems and Embodiments of the Invention]

Based on enthusiastic investigations carried out in order to achieve the above-mentioned aim, inventors of the invention have found that:

thermal deformation owing to the difference of the thermal expansion

20 coefficients of a substrate and patterns can be cancelled between the surface and the rear face; that warp of the substrate can be suppressed at the time of manufacturing the electrostatic chuck even if a thin and compact substrate is used; and that the electrostatically attracting force can be stabilized because of prevention of the thermal deformation and warp of the

25 electrostatic chuck or the electrostatic chuck provided with a heater at the

time of heating or cooling a wafer, by forming electrostatic chuck patterns in the surface of the supporting substrate and patterns same as or similar to the electrostatic chuck patterns in the rear face and more preferably, forming both patterns in the same thickness and accordingly, inventors of 5 the invention have accomplished the invention.

[0007]

That is, the invention provides: (1) an electrostatic chuck comprising electrode patterns for the electrostatic chuck bonded to the surface of a supporting substrate made of an insulating ceramic and patterns same as or 10 similar to the electrode patterns for the electrostatic chuck bonded to the rear face; (2) an electrostatic chuck (an electrostatic chuck provided with a heater) as described in (1) of which at least a portion of the patterns in the rear face are formed to be a heating part by being communicated with electric current; and (3) an electrostatic chuck as described in (1) or (2) of 15 which the electrode patterns for the electrostatic chuck in the surface and the patterns in the rear face are made of materials having thermal expansion coefficients substantially same as each other and further preferably, having the substantially same thickness.

[0008]

20 Hereinafter, the invention will be described in details. An electrostatic chuck of the invention, as shown in Fig. 1 and Fig. 2, comprises conductive electrode patterns 2 for the electrostatic chuck formed in the surface of a supporting substrate 1 made of an insulating ceramic and patterns 3 in the rear face. In this case, protection layers 4 are formed so 25 as to cover the respective patterns 2 and 3 in the surface and the rear face.

[0009]

With such a constitution in the invention, the above-mentioned front and rear patterns 2 and 3 are made to be same as or similar to each other as shown in Fig. 2 and Fig. 3.

5 [0010]

That the front and rear patterns 2 and 3 are same as or similar to each other means the basic shapes in the front and the rear faces (e.g. concentric, radial, spiral, combteeth-shaped shapes) are coincident with each other and it is preferable that: the positional difference of the intervals 10 of the front and rear patterns and the positional difference of the rims of the patterns are 2mm or smaller; and when the front and rear patterns are made to be stacked, the areas of portions where they are not overlapped is 30% or less of the areas of portions where they are overlapped. From such viewpoints, the front and rear patterns 2 and 3 shown in Fig. 1B and 1C and 15 the front and rear patterns 2 and 3 shown in Fig. 2B and 2C are similar to each other, however patterns shown in Fig. 3 are out of the scope of the invention since they have no pattern in the rear face. Also, the front and rear patterns 2 and 3 shown in Fig. 4 and Fig. 5 respectively are out of the scope of the invention since the front and rear patterns 2 and 3 are not 20 similar to each other.

[0011]

In this case, the above-mentioned patterns 2 in the surface side, as shown in Fig., can be formed by conventionally known patterning manner so as to be connected to an electric power source and have an electrostatic 25 chuck function by applying voltage. The illustrated patterns are so-called

bipolar shape patterns and the foregoing constitution is same with respect to the patterns with unipolar shapes.

[0012]

On the other hand, as shown in Fig. 1, the patterns 3 in the rear face 5 side may be composed of a plurality of respectively independent patterns 3a such as a plurality of concentric ring-like patterns or the like and particularly, the patterns 3 may be patterns 3a with no need of electrical connections to one another and as shown in Fig. 2C, the patterns 3 may be composed of heating patterns 3b and 3c composing heating parts by 10 connecting the heating patterns to an electric power source and applying voltage to them and in the case of an electrostatic chuck shown in Fig. 2, the electrostatic chuck is made to be an electrostatic chuck provided with a heater formed in the rear side.

[0013]

15 The above-mentioned front and rear patterns 2 and 3 are preferable to have the substantially same thickness. In such a case, the front and rear patterns 2 and 3 are formed to have a thickness of generally 10 to 500 μm , preferably 20 to 200 μm . That the front and rear patterns 2 and 3 have the substantially same thickness means that the difference of the 20 thickness between the front and rear patterns 2 and 3 is 100 μm or smaller, preferably 50 μm or smaller.

[0014]

25 The thickness of the above-mentioned substrate 1 is properly selected and it is generally 2 to 50 mm, preferably 10 to 30 mm and particularly in the invention, since problems such as warp are not caused

even if the substrate 1 is thin, the substrate can be made as thin as 5 mm or thinner.

[0015]

The thickness of the front and rear protection layers 4 is generally 5 to 2000 μm , preferably 50 to 1000 μm respectively. Moreover, it is preferable to form the front and rear protection layers 4 and 5 in such a manner that the front and rear protection layers have substantially same thickness and the difference of the thickness of the protection layers 4 is 300 μm or smaller, preferably 100 μm or smaller.

10 [0016]

A material for the above-mentioned substrate 1 may properly be selected among insulating ceramics and same materials as those conventionally used for electrostatic chucks can be used, however AlN, BN, a compounded body of AlN and BN, PBN, or SiO_2 is preferably used for the 15 substrate. In this case, AlN, BN, a compounded body of AlN and BN, PBN, or SiO_2 is preferably used also for formation of the above-mentioned front and rear protection layers 4 and especially, from a viewpoint that thermal expansion coefficients should be same, the front and rear protection layers 4 are preferable to be made of the same material and further these front and 20 rear protection layers 4 and the substrate 1 are preferable to be made of the same material.

[0017]

The electrode patterns 2 for the electrostatic chuck to be formed in the surface of the foregoing substrate 1 are made of a conductive material 25 and any conventional material that is used as a pattern forming material

can be used and generally, conductive ceramics such as SiC or the like, carbon, as well as metals of mainly W, Pt, Ag, Cu or the like can be exemplified.

[0018]

5 The patterns 3 to be formed in the rear face of the substrate 1 may be made of a material having a thermal expansion coefficient substantially same as that of the foregoing front patterns 2 above-mentioned, and especially, as described above, a conductive ceramic, carbon, and metals are preferable to be used for forming the patterns and the material

10 substantially same as that of the front patterns is especially preferable to be used. That the thermal expansion coefficient is substantially same means that the difference between the thermal expansion coefficients of the front and rear patterns 2 and 3 is generally $1 \times 10^{-3}/^{\circ}\text{C}$ or less, preferably $3 \times 10^{-6}/^{\circ}\text{C}$ or less.

15 [0019]

In such a manner, patterns for an electrostatic chuck are formed in the surface of a supporting substrate: the patterns same as or similar to the front patterns are formed in the rear face: preferably the front and rear patterns are made of materials having substantially same thermal

20 expansion coefficient each other and are formed in the same film thickness: and in the case of further forming protection layers, insulating layers made of a material same as that of the supporting substrate or having properties approximately same as those of the supporting substrate are formed as the protection layers and thus occurrence of warp in the manufacturing process

25 can be prevented and the heating or cooling capabilities for heating or

cooling a wafer can be improved and the stability at the time of heating and cooling can be improved.

[0020]

Incidentally, formation methods for the supporting substrate, the patterns, and the protection layers are not particularly limited and a variety of conventionally known methods can be employed, however it is preferable to form the supporting substrate by a chemical vapor deposition method or a crushing and sintering method and to form the patterns and the protection layers by a CVD method, a PVD method, a vacuum evaporation method. In such a case, these methods may be carried out according to conventionally known manners.

[0021]

[Examples]

Hereinafter, the invention will be described more particularly with reference to Examples and Comparative Examples, however the description is illustrative of the invention and is not to be construed as limiting the invention.

[0022]

[Example 1 and Comparative Example 1]

Supporting substrates with an outer diameter ϕ of 100 mm and a thickness of 2.5 or 10 mm and made of boron nitride by thermal decomposition were produced by reaction of ammonia and boron trichloride at 1800°C in 100 Torr or lower and then methane gas was thermally-decomposed under conditions of 2200°C and 5 Torr to form thermally-decomposed graphite layers thereon and the resulting substrates

were subjected to processing in the front and rear faces by an end mill to form patterns as shown in Fig. 1 to Fig. 5. Further, 200 μm -thick insulating layers of boron nitride produced by thermal decomposition were formed by reaction of ammonia and boron trichloride at 1800°C in 100 Torr

5 to produce 15 types of electrostatic chucks and electrostatic chucks provided with heaters which were different in the substrate thickness and the pattern shapes.

[0023]

Correlations between the substrate thickness and the warp after 10 production in the respective types of the patterns are shown in Fig. 6. Those having electrostatic chuck patterns formed concentrically in the surfaces of the supporting substrates and concentric patterns or heating patterns with the same shapes of the front patterns formed in the rear faces (Fig. 1 and Fig. 2) were found satisfactory to produce electrostatic chucks 15 and electrostatic chucks comprising heaters with little warp even if the thickness of the substrates was as thin as 2 mm.

[0024]

[Example 2 and Comparative Example 2]

The surfaces of electrostatic chucks comprising substrates with 2 20 mm thickness and patterns as shown in Fig. 1 and Fig. 2 and electrostatic chucks comprising substrates with 10 mm thickness and patterns as shown in Fig. 4 produced in Example 1 and Comparative Example 1 were subjected to finishing grinding and the temperature dependency of the electrostatic attraction force of each electrostatic chuck was measured by applying 25 voltage of 500 V.

[0025]

As a result, those comprising substrates with 10 mm thickness and patterns as shown in Fig. 4 and those comprising substrates with 2 mm thickness and patterns as shown in Fig. 1 and Fig. 2 were found capable of 5 giving approximately constant attracting force in the entire temperature range from a room temperature to 400°C. Accordingly, it is confirmed that even if the thickness of a substrate is made thin, stable electrostatically attracting force can be obtained in the case an electrostatic chuck is 10 designed in consideration of the similarity of the shapes of the front and rear patterns.

[0026]

[Example 3 and Comparative Example 3]

After supporting substrates with an outer diameter ϕ of 100 mm and a thickness of 2 mm and made of boron nitride by thermal decomposition 15 were produced in the same manner as Example 1 and Comparative Example 1200 μm -thick graphite layers were formed by thermal decomposition and electrostatic chuck patterns were formed concentrically in the surfaces and heating patterns with the same diameters as those of the patterns in the surfaces were formed concentrically in the rear faces by using an end mill. 20 After that, the conductive layers so as to compose the electrostatic chucks were ground by sand paper to finish them in a thickness of 20 μm . After that, insulating layers of boron nitride produced by thermal decomposition were formed to produce electrostatic chucks provided with heaters and comprising the front and rear conductive layers with different thickness and 25 their warp after the production was compared with the warp of electrostatic

chucks provided with heaters and comprising the conductive layers without grinding, that is having the same thickness of the conductive layers in the front and rear faces.

[0027]

5 As a result, in the case the thickness of the conductive layers was same in the front and rear faces, the warp was 50 μm , meanwhile in the case the thickness of the conductive layers composing the electrostatic chucks was 20 μm , the warp was 300 μm . The deformation was supposedly attributed to the thermal stress and the difference of the thickness of the 10 conductive layers caused by difference of the thermal expansion coefficients of the conductive layers and the substrate and consequently, it is confirmed that the thickness of the front and rear conductive layers is preferable to be same.

[0028]

15 [Example 4 and Comparative Example 4]

After supporting substrates with an outer diameter ϕ of 100 mm and a thickness of 2 mm and made of boron nitride by thermal decomposition were produced in the same manner as Example 1 and Comparative Example 1, 100 μm -thick graphite layers were formed by thermal decomposition in 20 the surfaces and 100 μm -thick Pt layers were formed in the rear faces by vapor deposition method and electrostatic chuck patterns were formed concentrically in the surfaces and heating patterns with the same diameters as those of the patterns in the surfaces were formed concentrically in the rear faces by using an end mill. After that, 200 μm -thick insulating layers 25 of boron nitride were formed on the front and rear conductive layers to

produce electrostatic chucks provided with heaters and comprising the front and rear conductive layers of the different materials and their warp after the production was compared with the warp of electrostatic chucks provided with heaters and comprising the front and rear conductive layers both of

5 which were 100 μm graphite layers formed by thermal decomposition.

[0029]

As a result, the warp of the latter was 50 μm , and on the other hand, the warp of the former was 500 μm , considerably significant as compared with the warp of the latter. That is supposedly attributed to the difference 10 of the thermal expansion coefficients of the materials of the front and rear conductive layers and accordingly, it is confirmed that the materials for the front and rear conductive layers are preferably same.

[0030]

[Effects of the Invention]

15 According to the invention, with respect to an electrostatic chuck, more particularly an electrostatic chuck provided with a heater and having a heating function, for electrostatically attracting a wafer or the like to be a supporting substrate of a semiconductor device, wherein electrostatic chuck patterns are formed on the surface of the supporting substrate and patterns 20 or heating patterns same as or similar to the electrostatic chuck patterns are formed on the rear face, so that warp can be suppressed in the manufacturing process even if the substrate is thin and compact. Also, thermal deformation and warp of the electrostatic chuck or the electrostatic chuck provided with a heater can be prevented when a wafer is heated or 25 cooled and thus the electrostatic attraction power can be stabilized.

Consequently, an electrostatic chuck and an electrostatic chuck provided with a heater with excellent properties and capabilities can be provided at a low cost.

[Brief Descriptions of the Drawings]

5 Fig. 1 shows a first Example of the invention. Fig. 1A is a cross-sectional view along the A-A line of Fig. 1B and 1C: Fig. 1B is a top view: and Fig. 1C is a back view.

10 Fig. 2 shows a second Example of the invention. Fig. 2A is a cross-sectional view along the A-A line of Fig. 2B and 2C: Fig. 2B is a top view: and Fig. 2C is a back view.

Fig. 3 shows a first comparative example. Fig. 3A is a cross-sectional view along the A-A line of Fig. 3B and 3C: Fig. 3B is a top view: and Fig. 3C is a back view.

15 Fig. 4 shows a second comparative example. Fig. 4A is a cross-sectional view along the A-A line of Fig. 4B and 4C: Fig. 4B is a top view: and Fig. 4C is a back view.

Fig. 5 shows a third comparative example. Fig. 5A is a cross-sectional view along the A-A line of Fig. 5B and 5C: Fig. 5B is a top view: and Fig. 5C is a back view.

20 Fig. 6 is a graph showing the correlations between the thickness of the substrates and the warp in electrostatic chucks of Examples and Comparative Examples shown in Fig. 1 to Fig. 5.

[Explanation of Symbols]

1 a substrate

25 2 electrode patterns of an electrostatic chuck

3 patterns

4 protection layers

Translation of the figure

5 [Fig. 6]

lateral axis: warp (μm)

longitudinal axis: substrate thickness (mm)

---▲--- the electrostatic chuck of Fig. 1

---△--- the electrostatic chuck of Fig. 2

10 ---●--- the electrostatic chuck of Fig. 3

---○--- the electrostatic chuck of Fig. 4

---□--- the electrostatic chuck of Fig. 5

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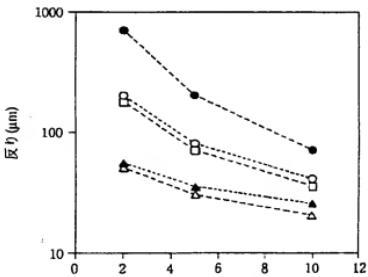
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信越化學工業株式会社
東京都千代田区大手町二丁目6番1号
(72)発明者 猪野 正樹
群馬県安中市礪部2丁目13番1号 信越化
學工業株式会社精密機能材料研究所内
(72)発明者 黒沢 幸夫
群馬県安中市礪部2丁目13番1号 信越化
學工業株式会社群馬事業所内
(72)発明者 新井 延男
群馬県安中市礪部2丁目13番1号 信越化
學工業株式会社群馬事業所内
(74)代理人 弁理士 小島 隆司 (外1名)

(54)【発明の名称】 静電チャック

(57)【要約】

【解決手段】 電気絶縁性セラミックスからなる支持基板の表面に静電チャック用電極パターンが接合されると共に、裏面に上記静電チャック用電極パターンと同一又は類似形状のパターンが接合されていることを特徴とする静電チャック。

【効果】 本発明によれば、半導体装置の基板となるウエハー等を静電気を利用して吸着する静電チャック、更には加熱機能を合わせ持つヒーター付静電チャックにおいて、その支持基板裏面に静電チャックパターンが形成され、裏面には該パターンと同じ又は類似形状のパターン又は発熱パターンが形成されることにより、基板が薄くコンパクトでもその製造時の反りの発生が抑制され、またウエハーが加熱又は冷却される際に静電チャック及びヒーター付静電チャックの熱変形及び反り等が発生せずに静電吸着力が安定するという有利性が与えられ、低成本で性能の優れた静電チャック及びヒーター付静電チャックを供給することができる。



▲---▲ 図1のチャック
△---△ 図2のチャック
●---● 図3のチャック
○---○ 図4のチャック
□---□ 図5のチャック

〔特許請求の範囲〕

〔請求項1〕 電気絶縁性セラミックスからなる支持基板の表面に静電チャック用電極パターンが接合されると共に、裏面に上記静電チャック用電極パターンと同一又は類似形状のパターンが接合されていることを特徴とする静電チャック。

〔請求項2〕 上記裏面のパターンの少なくとも一部が、電源に接続されることにより発熱部として構成される発熱パターンである請求項1記載の静電チャック。

〔請求項3〕 上記表面の静電チャック用電極パターンと裏面のパターンとが互いに実質的に同じ熱膨張係数を有する材料により形成された請求項1又は2記載の静電チャック。

〔請求項4〕 上記表面の静電チャック用電極パターンと裏面のパターンとが互いに実質的に同じ厚さを有する請求項1、2又は3記載の静電チャック。

〔請求項5〕 支持基板がA1N、BN、AlNとBNとの複合体、PBN又はSiO₂にて形成された請求項1乃至4のいずれか1項記載の静電チャック。

〔請求項6〕 支持基板が化学気相蒸着法又は粉末焼結法により形成されると共に、裏面のパターンがそれぞれ化学気相蒸着法により形成された請求項1乃至5のいずれか1項記載の静電チャック。

〔請求項7〕 上記表面のパターンをそれぞれ複数の支持基板と実質的に同じ熱膨張係数を有する保護層を形成した請求項1乃至6のいずれか1項記載の静電チャック。

〔請求項8〕 保護層がAlN、BN、AlNとBNとの複合体、PBN又はSiO₂にて形成された請求項7記載の静電チャック。

〔請求項9〕 保護層が化学気相蒸着法により形成された請求項7又は8記載の静電チャック。

〔発明の詳細な説明〕

〔0001〕

〔発明の属する技術分野〕 本発明は、半導体装置の基板となるウエハ等を静電気を利用して吸着する静電チャック及び加熱の機能を合わせ持つヒーター付静電チャックに関する。

〔0002〕

〔従来の技術及び発明が解決しようとする課題〕 近年の半導体素子の製造工程の中で、静電チャックは分子線エビタキシーやCVD、スパッタリング、エッチングなどでウエハを静電吸着して支持するために用いられており、この静電チャックはプロセスの高温化に伴ってその材質は樹脂からセラミックスに移行している（特開昭52-67353号公報、特開昭59-124140号公報参照）。また、最近ではセラミックヒーターと静電チャックを合体した静電チャック付セラミックスヒーターも提案されている（特開平5-109875号公報、特開平5-129210号公報参照）。

〔0003〕 この場合、分子線エビタキシーやCVD、スパッタリング等において、成膜を行うに際しては、ウエハの温度が膜の性質、成膜速度に大きな影響があるため、ウエハの均熱性の向上が求められている。また、ドライエッティングにおいては、ウエハの温度が微細エッティング時のエッティング形状、選択性、分布等に大きな影響があるため、ウエハを冷却するための冷却性能の向上が求められている。

〔0004〕 この静電チャックを製造する際、基板に静電チャック用電極パターンを接合し、更に絶縁層を設けるが、該基板及び絶縁層とパターン層の材質が相違し、特に熱膨張率が異なるために、製造時の熱履歴で反りが発生し、その反りが大きいと絶縁層の表面を研磨仕上げする時に一部のパターン層が表面に現れたり、もしくは現れないにしても絶縁層の絶縁耐圧が低下して不良品となってしまう。また、うまく研磨仕上げできたとしても、ウエハを加熱及び冷却する際にこの熱膨張率差から起因した静電チャックの熱変形又は反りが発生し、その結果、静電チャックの加熱又は冷却時に吸着力が安定しないことが懸念されていた。これを解決する手段としては、基板を厚くすればよいが、熱容量が大きくなるため消費電力が増大し、さらには昇温降温にも時間がかかり、またコスト的にも高くなってしまうため、なるべく薄くコンパクトなものが望まれていた。しかし、薄くすると上述の問題が発生してしまうため、基板を厚くせざるを得なかった。

〔0005〕 本発明は上記事情を改善するためになされたもので、基板が薄くコンパクトなものでも製造時の反りが小さく、しかも低温から高温まで安定した静電吸着力が得られる静電チャック及びヒーター付静電チャックを提供することを目的とする。

〔0006〕

〔課題を解決するための手段及び発明の実施の形態〕 本発明者は、上記目的を達成するため銳意検討を行った結果、支持基板表面に静電チャックパターンを形成すると共に、裏面にこの静電チャックパターンと同一又は類似形状のパターンを形成すること、この場合、好ましくは両パターンを実質的に同じ厚さに形成することにより、基板とパターンの熱膨張率差による熱変形が表裏で相殺し、基板が薄くコンパクトなものでもその製造時の反りの発生が抑制され、またウエハが加熱又は冷却される際に該静電チャック及び該ヒーター付静電チャックの熱変形及び反り等が発生せずに静電吸着力が安定することを知見し、本発明をなすに至った。

〔0007〕 即ち、本発明は、（1）電気絶縁性セラミックスからなる支持基板の表面に静電チャック用電極パターンが接合されると共に、裏面に上記静電チャック用電極パターンと同一又は類似形状のパターンが接合されていることを特徴とする静電チャック、（2）上記裏面のパターンの少なくとも一部が、電流が流されるることに

より発熱部として構成される発熱パターンである上記（1）記載の静電チャック（ヒーター付静電チャック）、（3）上記表面の静電チャック用電極パターンと裏面のパターンとが互いに実質的に同じ熱膨張係数を有する材質にて形成され、更に好ましくは実質的に同じ厚さを有する上記（1）又は（2）記載の静電チャックを提供する。

【0008】以下、本発明につき更に詳しく述べる。本発明の静電チャックは、図1及び図2に示すように、電気絶縁性セラミックスからなる支持基板1の表面に導電性を有する静電チャック用電極パターン2が形成されていると共に、裏面にもパターン3が形成されたものである。この場合、上記表裏のパターン2、3をそれぞれ覆して保護層4が形成される。

【0009】本発明は、このような構成において、上記表裏のパターン2、3を図2、3に示すように互いに同一又は類似の形状としたものである。

【0010】ここで、表裏のパターン2、3が同一又は類似とは、表裏基本形状（例えば同心円状、放射状、渦巻状、樹状）が一致し、表裏パターン間隔、パターン線等のずれが2mm以下で、かつ表裏パターンを重ね合わせた時、重複していない部分の面積が重複している部分のその30%以下であることが望ましい。このような点から、図1（b）、（c）の表裏パターン2、3、図2（b）、（c）の表裏パターン2、3は互いに類似であるが、図3は裏面にパターンが形成されていないので、これは勿論本発明の範囲外であり、また図4、5はそれぞれ表裏のパターン2、3が類似していないもので、本発明の範囲外である。

【0011】この場合、上記表面側のパターン2は、図示したように、電源と接続されて電圧が印加されることにより、静電チャック機能が発生されるように公知のパターン方式に従って形成することができる。ここで、図示したものは双極形といわれているパターンであるが、単極形でも同様である。

【0012】一方、裏面側のパターン3は、図1に示すように、複数のリング状パターンが同心状に形成されるなど、複数のパターン3aが相互に独立して形成され、特に相互のパターン3aとの電気的接続を考慮しないパターンとしてらしく、また、図2（c）に示すように、電源に接続されて電圧を印加されることにより、発熱部を構成する発熱パターン3b、3cとして形成することもでき、図2の静電チャックの場合は裏面側がヒーターとなるヒーター付静電チャックとして形成される。

【0013】また、上記表裏のパターン2、3は互いにその厚さが実質的に同一であることが望ましい。この場合、これら表裏のパターン2、3は通常10～500μm、特に20～200μmの厚さに形成されるが、表裏のパターン2、3が実質的に同じ厚さを有するとは、表裏のパターン2、3の厚さの差が100μm以下のこと

であり、特に50μm以下であることが好ましい。

【0014】なお、上記基板1の厚さは適宜選定され、通常2～50mm、特に10～30mmに形成し得るが、本発明においては、基板1が薄くても反り等の問題が生じないので、5mm以下の厚さに形成し得る。

【0015】また、上記表裏の保護層4の厚さは、それぞれ10～2000μm、特に50～1000μmとすることが好ましく、しかもこの場合、表裏の保護層4、5は互いに実質的に同じ厚さで、即ち保護層4の厚さの差が300μm以下、特に100μm以下となるように形成することが好ましい。

【0016】上記基板1の材質も電気絶縁性セラミックの中から適宜選定することができ、従来の静電チャックの基板と同様の材質にて形成し得るが、特にA1N、BN、AINとBNとの複合体、PBN又はSiO₂にて形成することが好ましい。この場合、上記表裏の保護層4もA1N、BN、AINとBNとの複合体、PBN又はSiO₂にて形成することが好ましく、特に熱膨張係数を同じにするという点から、表裏の保護層4は互いに同じ材質にて形成することが好ましく、更にはこれら表裏の保護層4と基板1とは同じ材質とすることが好ましい。

【0017】一方、上記基板1の表面に形成される静電チャック用電極パターン2は、導電性材料にて形成されるが、その材質としては公知のパターン形成材料を用いることができ、通常SiC等の導電性セラミックス、カーボン、それにW、Pt、Ag、Cu等を主とした金属にて形成することができる。

【0018】また、基板1の裏面に形成されるパターン3は、好ましくは上記表面のパターン2と実質的に同じ熱膨張係数を有する材質にて形成することができ、具体的には上記と同様の導電性セラミックス、カーボン、金属にて形成することが好適であり、特に表面のパターンと同じ材質にて形成することが好ましい。なお、実質的に同じ熱膨張係数とは、表裏のパターン2、3の熱膨張係数の差が $1 \times 10^{-4}/^{\circ}\text{C}$ 以下、特に $3 \times 10^{-4}/^{\circ}\text{C}$ 以下であることが好ましい。

【0019】このように支持基板表面に静電チャック用パターンを形成し、裏面に表面パターンと同一又は類似形状のパターンを形成し、好ましくは表裏のパターンを実質的に同じ熱膨張係数を有する材質、膜厚にて形成し、更には保護層を形成した場合には、これを支持基板と同じ材質又は同程度の特性の絶縁層とすることにより、製造時の反りの発生の防止、ウェーハを加熱又は冷却する加熱性能又は冷却性能の向上、加熱又は冷却時の安定性の向上を達成し得るものである。

【0020】なお、支持基板、パターン、保護層の形成方法は特に制限されず、公知の種々の方法を採用し得るが、支持基板は化学気相蒸着法や粉体焼結法により形成し、またパターン及び保護層はCVD法、PVD法、真

空蒸着法等によって形成することができる。この場合、これら方法は常法に従って行うことができる。

〔0021〕

〔実施例〕以下、実施例と比較例を示し、本発明を具体的に説明するが、本発明は下記の実施例に制限されるものではない。

〔0022〕〔実施例1、比較例1〕アンモニアと三塩化硼素とを100Torr下に1800°Cで反応させて外径φ100mm、厚さ2、5又は10μmの熱分解窒化硼素製支持基板を作製し、次いでメタンガスを2200°C、5Torrの条件下で熱分解してこれに厚さ100μmの熱分解グラファイト層を形成し、表面と裏面に図1～5のようなバターンをエンジルを用いて加工した。更に、アンモニアと三塩化硼素とを100Torr下に1800°Cで反応させて厚さ200μmの熱分解窒化硼素絶縁層を設けて、基板厚さ及びバターン形状の異なる15種類の静電チャック及びヒーター付静電チャックを作製した。

〔0023〕それぞれのバターン種の基板厚さと製造後の反りの関係を図6に示す。支持基板表面の静電チャックバターンが同心円状に形成され、裏面に該バターンと同形の同心円状のバターン又は発熱バターンを形成したもの（図1及び図2）は基板厚が2mmと薄くても反りの少ない良好な静電チャック及びヒーター付静電チャックを作製することができることが認められた。

〔0024〕〔実施例2、比較例2〕実施例1、比較例1で作製したもののうち基板厚2mmで図1及び図2のものと基板厚10μmで図4のものの表面を研磨仕上げして、印加電圧を500Vとしてそれぞれの静電吸着力の温度依存性を測定した。

〔0025〕その結果、室温から400°Cまで基板厚10mmで図4のバターンのものと基板厚2mmで図1、2のバターンのものは、すべての温度域において同程度の吸着力が得られた。このことより、基板厚を薄くしてもバターン形状の裏裏の類似性を考慮して設計すれば、安定した静電吸着力が得られることが確認できた。

〔0026〕〔実施例3、比較例3〕実施例1、比較例1と同様の方法で外径φ100mm、厚さ2mmの熱分解窒化硼素製支持基板を作製した後、厚さ200μmの熱分解グラファイト層を形成し、表面に静電チャックバターンを同心円状に、裏面には表面バターンと同径の同心円状の発熱バターンをエンジルを用いて加工した。その後、静電チャックとなる導電層をサンドベーパー研磨して、20μmの厚さに仕上げた。次いで、熱分解窒化硼素絶縁層を設けて裏裏導電層厚さの異なるヒーター付静電チャックを作製し、静電チャックとなる導電層を研磨していない、つまり導電層厚さが裏裏等しいヒーター付静電チャックとの製造後の反りを比較した。

〔0027〕その結果、裏裏導電層の厚さが同じ場合の反りが50μmであるのに対し、静電チャックとなる

導電層が20μmの時の反りは300μmとなってしまった。この変形は、導電層と裏裏の熱膨張率が異なり、その差によって発生する熱応力と導電層の厚さが関与していると考えられ、従って、裏裏導電層厚さが同じであることが好ましいことが認められた。

〔0028〕〔実施例4、比較例4〕実施例1、比較例1と同様の方法で外径φ100mm、厚さ2mmの熱分解窒化硼素製支持基板を作製した後、表面には厚さ100μmの熱分解グラファイト層を形成し、裏面には厚さ100μmのPt層を真空蒸着により形成し、表面に静電チャックバターンを同心円状に、裏面には表面バターンと同径の同心円状の発熱バターンをエンジルを用いて加工した。次いで、裏裏導電層上に厚さ200μmの窒化硼素絶縁層を設けて裏裏導電層の材質の異なるヒーター付静電チャックを作製し、裏裏導電層とも厚さ100μmの熱分解グラファイト層でできたヒーター付静電チャックとの製造後の反りを比較した。

〔0029〕その結果、後者の反りが50μmであるのに対し、前者は後者より大きくなり、反りは500μmとなってしまった。これは、裏裏導電層の熱膨張率差が関与していると考えられ、従って、裏裏導電層の材質が同じであることが好ましいことが認められた。

〔0030〕

〔発明の効果〕本発明によれば、半導体製造の基板となるウエハ等を静電気を利用して吸着する静電チャック、更には加熱機能を合わせ持つヒーター付静電チャックにおいて、その支持基板表面に静電チャックバターンが形成され、裏面には該バターンと同じ又は類似形状のバターン又は発熱バターンが形成されることにより、基板が薄くコンパクトでもその製造時の反りの発生が抑制され、またウエハが加熱又は冷却される際に静電チャック及びヒーター付静電チャックの熱変形及び反り等が発生せずに静電吸着力が安定するという有利性が与えられ、低コストで性能の優れた静電チャック及びヒーター付静電チャックを供給することができる。

〔図面の簡単な説明〕

〔図1〕本発明の第1の実施例を示し、(a)は(b)、(c)のA-A線に沿った断面図、(b)は平面図、(c)は裏面図である。

〔図2〕本発明の第2の実施例を示し、(a)は(b)、(c)のA-A線に沿った断面図、(b)は平面図、(c)は裏面図である。

〔図3〕本発明の第1の比較例を示し、(a)は(b)、(c)のA-A線に沿った断面図、(b)は平面図、(c)は裏面図である。

〔図4〕本発明の第2の比較例を示し、(a)は(b)、(c)のA-A線に沿った断面図、(b)は平面図、(c)は裏面図である。

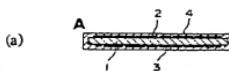
〔図5〕本発明の第3の比較例を示し、(a)は(b)、(c)のA-A線に沿った断面図、(b)は平面図、(c)は裏面図である。

面図 (c) は裏面図である。

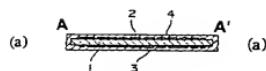
〔図6〕図1～5の実施例、比較例の静電チャックにおける基板厚さと反りの関係を示すグラフである。

〔符号の説明〕

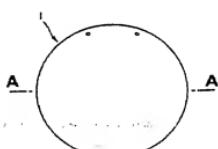
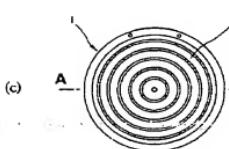
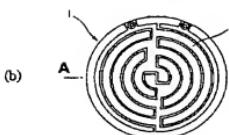
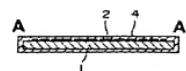
〔図1〕



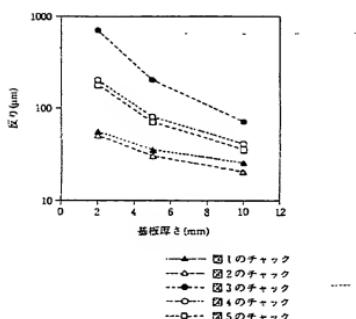
〔図2〕



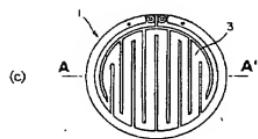
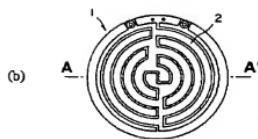
〔図3〕



〔図6〕



〔図4〕



〔図5〕

